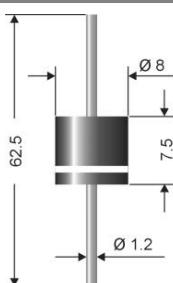


# HE 12FA ... HE 12FD



## Axial lead diode

High efficiency fast silicon rectifier diode

**HE 12FA...HE 12FD**

**Forward Current: 12 A**

**Reverse Voltage: 50 to 200 V**

## Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

## Mechanical Data

- Plastic case 8 x 7,5 [mm]
- Weight approx.: 1,5 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 500 pieces per ammo

1) Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

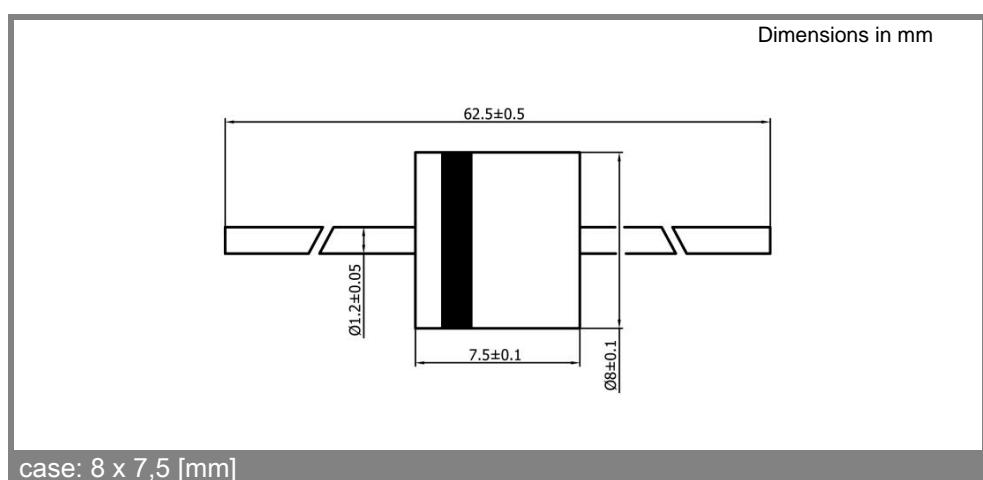
2)  $I_F = 5 \text{ A}$ ,  $T_J = 25 \text{ }^\circ\text{C}$

3)  $T_A = 25 \text{ }^\circ\text{C}$

Type	Repetitive peak reverse voltage $V_{RRM}$ V	Surge peak reverse voltage $V_{RSM}$ V	Max. reverse recovery time $I_F = 0,5 \text{ A}$ $I_R = 1 \text{ A}$ $I_{RR} = 0,25 \text{ A}$ $t_{rr}$ ns	Max. forward voltage $V_F^{(2)}$
HE 12FA	50	50	200	0,82
HE 12FB	100	100	200	0,82
HE 12FD	200	200	200	0,82

Absolute Maximum Ratings		$T_A = 25 \text{ }^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$I_{FAV}$	Max. averaged fwd. current, R-load, $T_A = 50 \text{ }^\circ\text{C}$ <sup>1)</sup>	12	A
$I_{FRM}$	Repetitive peak forward current $f > 15 \text{ Hz}$ <sup>1)</sup>	80	A
$I_{FSM}$	Peak forward surge current 50 Hz half sinus-wave <sup>3)</sup>	375	A
$i^2t$	Rating for fusing, $t < 10 \text{ ms}$ <sup>3)</sup>	680	A <sup>2</sup> s
$R_{thA}$	Max. thermal resistance junction to ambient <sup>1)</sup>	12	K/W
$R_{thT}$	Max. thermal resistance junction to terminals <sup>1)</sup>	-	K/W
$T_j$	Operating junction temperature	-50...+150	°C
$T_s$	Storage temperature	-50...+175	°C

Characteristics		$T_A = 25 \text{ }^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$I_R$	Maximum leakage current, $T_j = 25 \text{ }^\circ\text{C}$ ; $V_R = V_{RRM}$	<25	µA
	$T_j = \text{°C}$ ; $V_R = V_{RRM}$		
$C_J$	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
$Q_{rr}$	Reverse recovery charge ( $U_R = V$ ; $I_F = A$ ; $dI_F/dt = A/\text{ms}$ )	-	µC
$E_{RSM}$	Non repetitive peak reverse avalanche energy ( $I_R = mA$ ; $T_j = \text{°C}$ ; inductive load switched off)	-	mJ



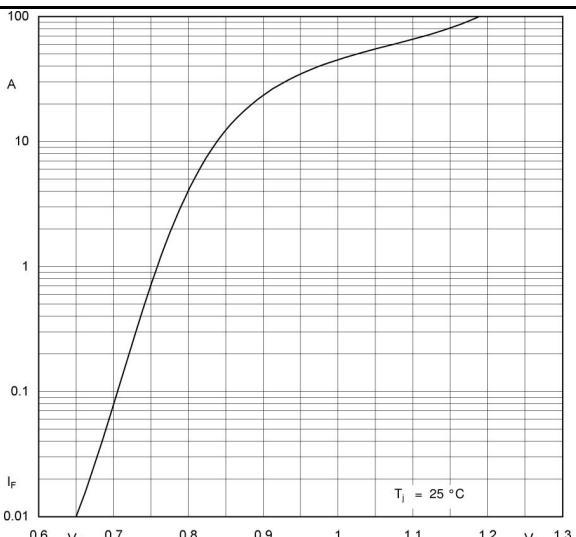


Fig. 1 Forward characteristic ( typical values ) <sup>1)</sup>

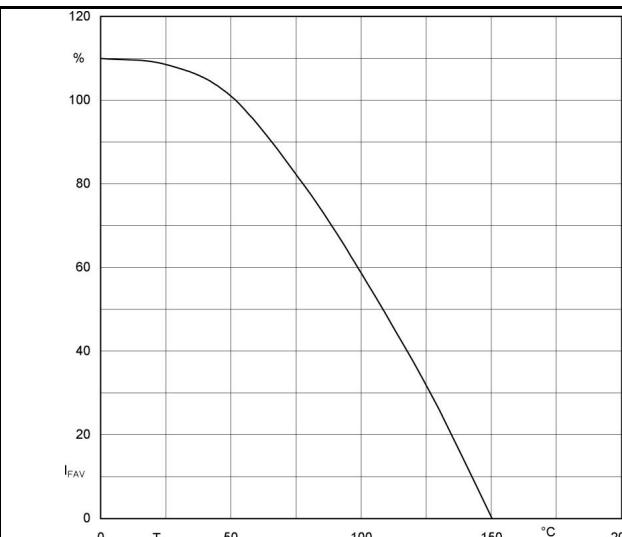


Fig. 2 Rated forward current vs. ambient temperature <sup>1)</sup>

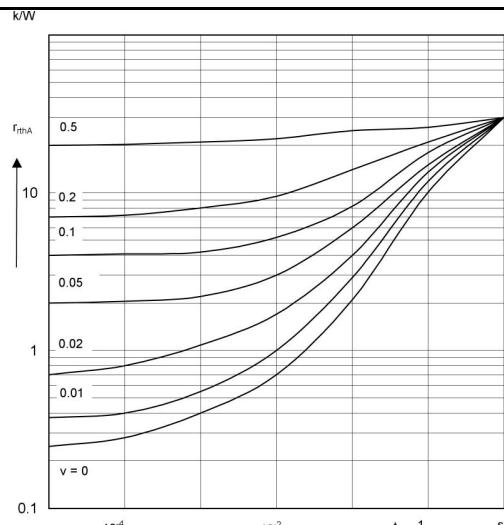


Fig. 3 Pulse thermal resistance vs. pulse duration <sup>1)</sup>